



Nikhef

# Digital Pixel Test Structure characterization with the ALPIDE telescope



ALICE

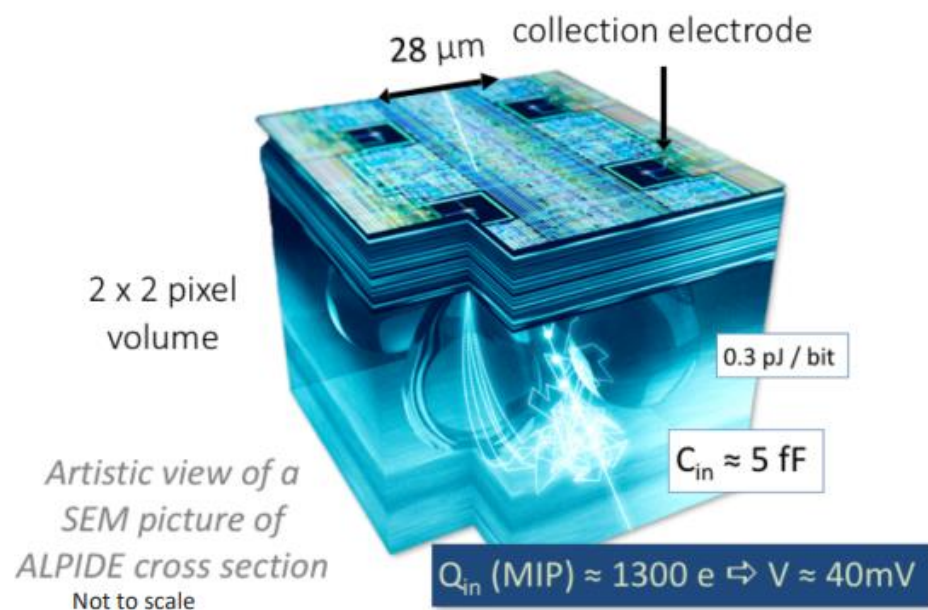
UNIVERSITEIT  
VAN AMSTERDAM

Roberto Russo, on behalf of ALICE  
BTTB10, 22.06.2022



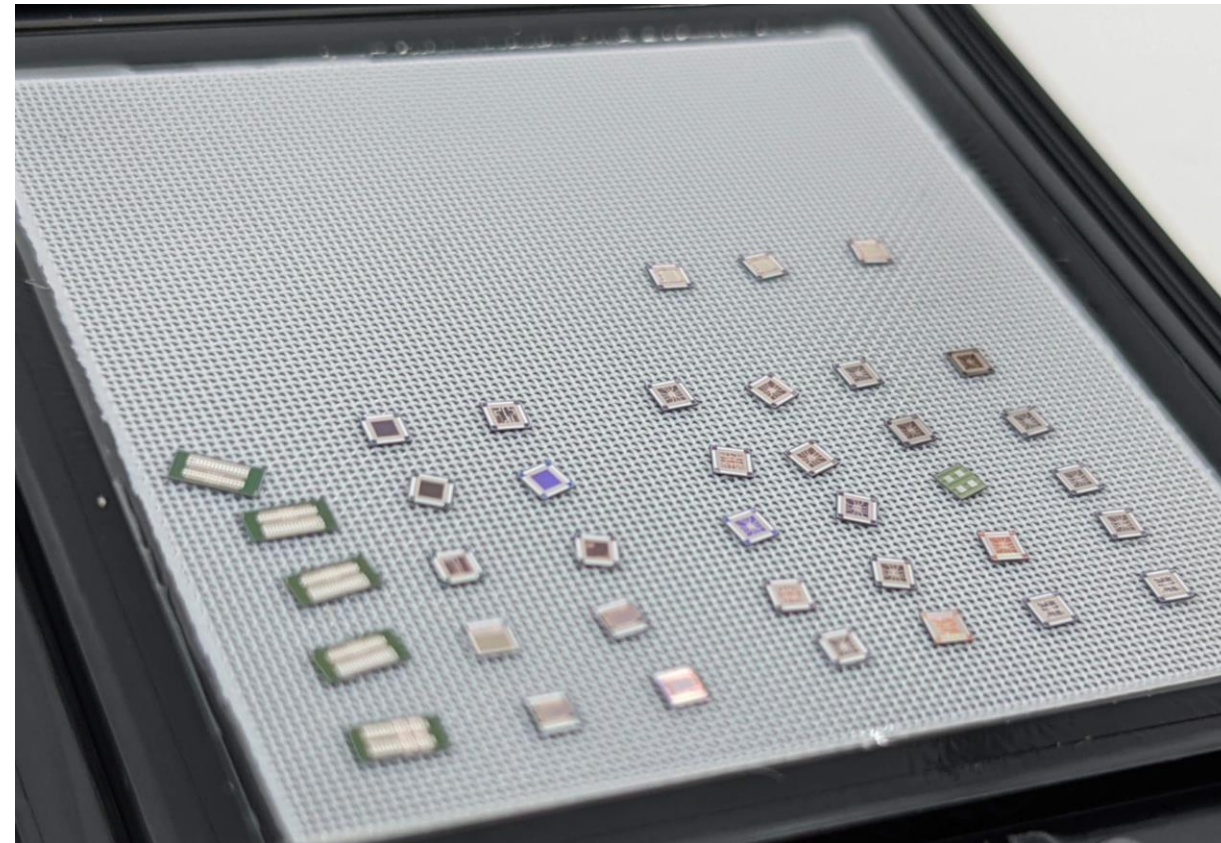
# Motivation

- Development and characterization of sensors for the ALICE Inner Tracking System (ITS) upgrade
  - Monolithic CMOS pixel sensors (MAPS) with small collection electrode
  - Low noise, low power consumption, reduced material budget
  - ALPIDE (ALice Pixel DEtector) chip (180 nm CMOS MAPS) is the base of the current tracker
  - It is the starting point for the ITS3 development



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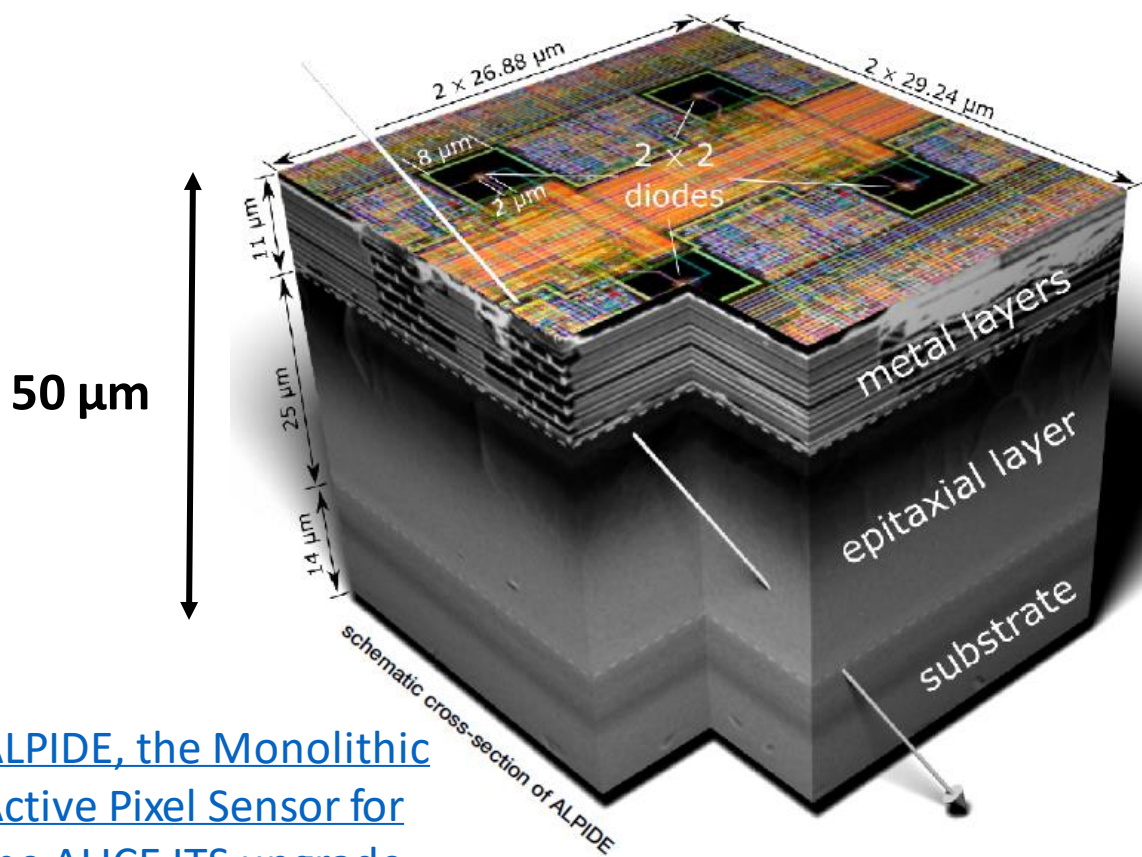
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  - ALPIDE (ALice Pixel DEtector) chip (180 nm CMOS MAPS) is the base of the current tracker
  - It is the starting point for the ITS3 development
- Target technology for ITS3 is 65 nm CMOS process (12 inch wafers)
  - Several test structures available for testing
    - APTS, **DPTS**, CE65, ...
  - Intensive laboratory and testbeam characterization effort
  - Flexible and advanced tools required





# The ALPIDE telescope

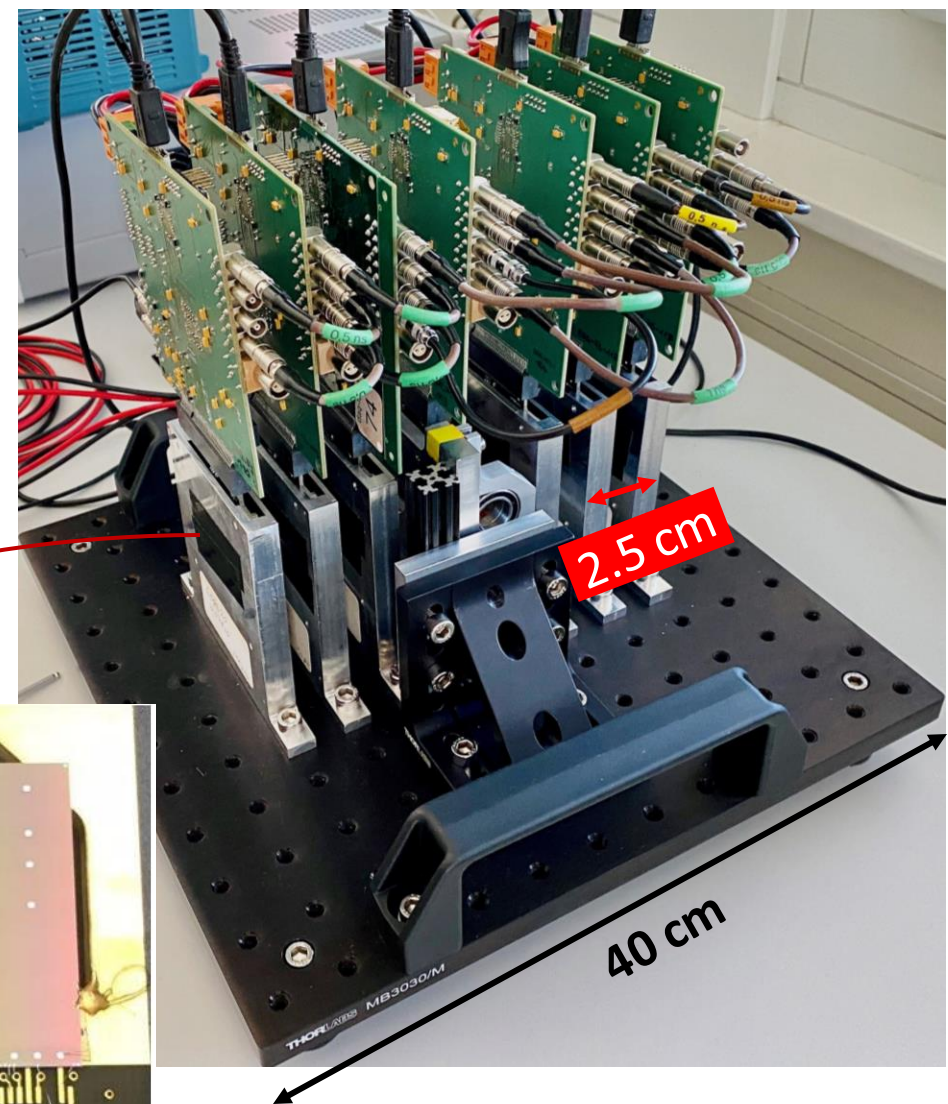
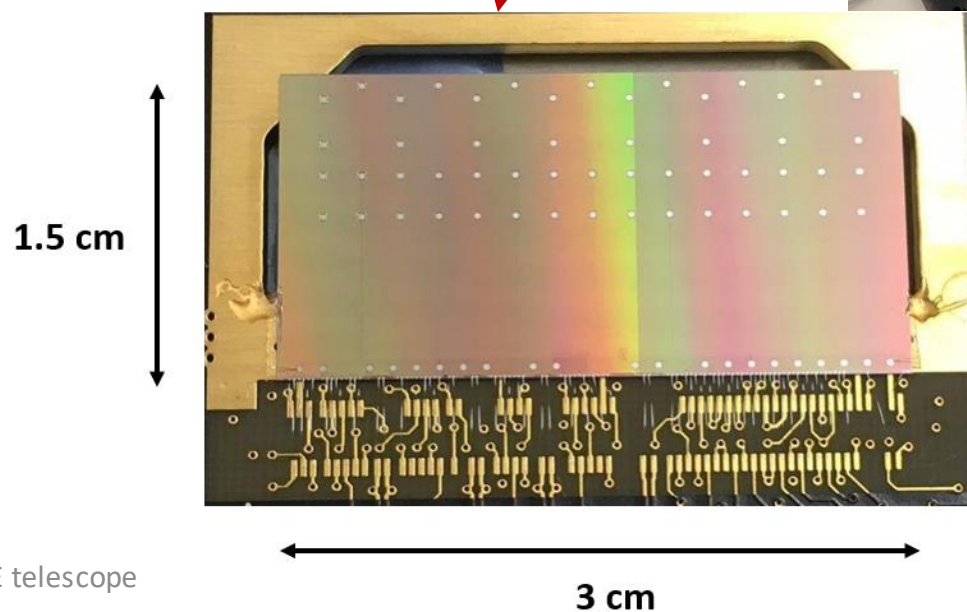
- Based on the ALPIDE chip
  - 1024 × 512 pixels, 29 μm × 27 μm pixel size
  - Reduced material budget (50 μm of silicon per plane)
  - 5 μm spatial resolution
  - Detection efficiency above 99.99%



[ALPIDE, the Monolithic Active Pixel Sensor for the ALICE ITS upgrade](#)

# The ALPIDE telescope

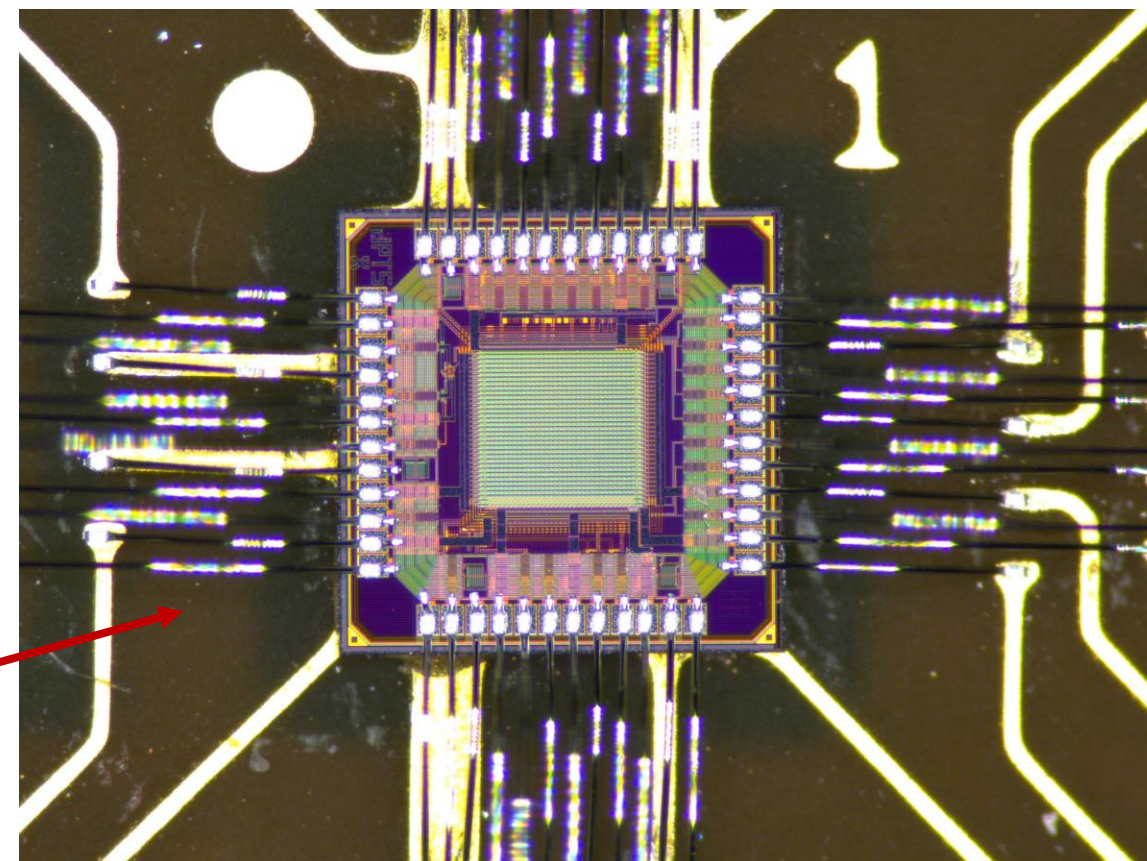
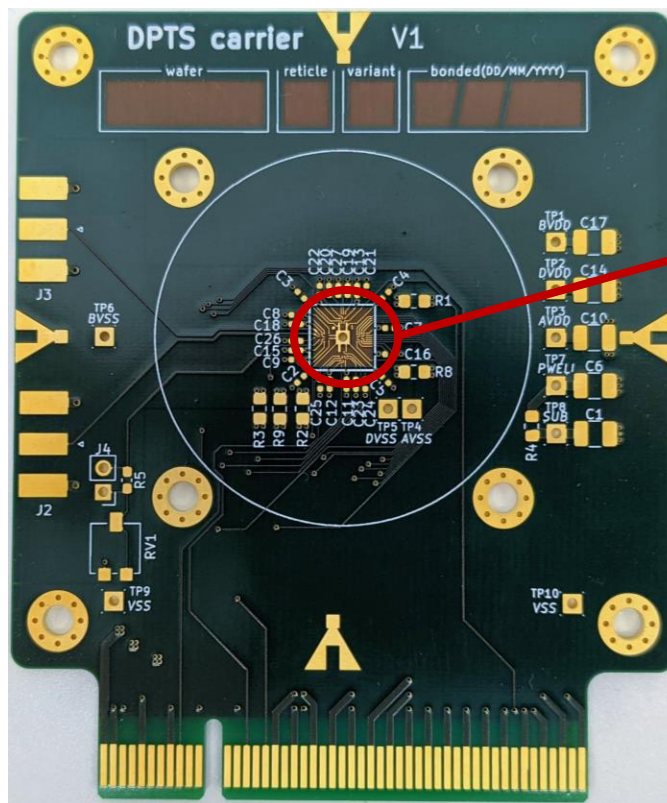
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  - 1024 × 512 pixels, 29 μm × 27 μm pixel size
  - Reduced material budget (50 μm of silicon per plane)
  - 5 μm spatial resolution
  - Detection efficiency above 99.99%
- 6 ALPIDE tracking planes as standard configuration
  - 3 planes before the Device(s) Under Test (DUT)
  - 3 planes after the DUT(s)
  - 2.5 cm distance between planes
  - 3 μm tracking resolution on the DUT plane
- Designed for high flexibility and portability





# Digital Pixel Test Structure (DPTS)

- Test structure of the first chips submission in TPSCo (Tower Partners Semiconductor Co) 65 nm CMOS imaging process
- $32 \times 32$  pixels,  $15 \mu\text{m}$  pixel pitch
- $50 \mu\text{m}$  silicon thickness
- Asynchronous digital readout with Time over Threshold (ToT) information
- Time-based encoding of the hit position

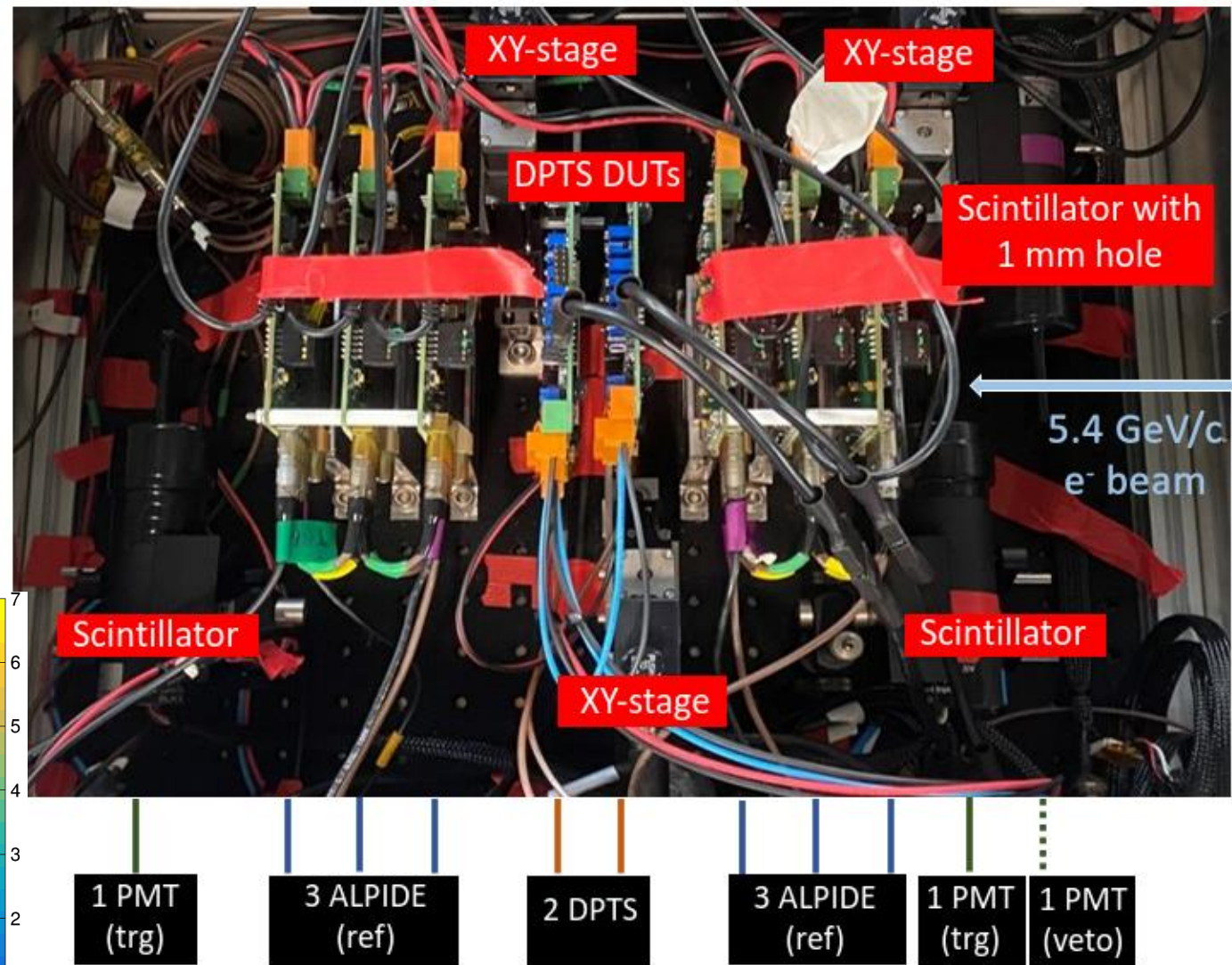
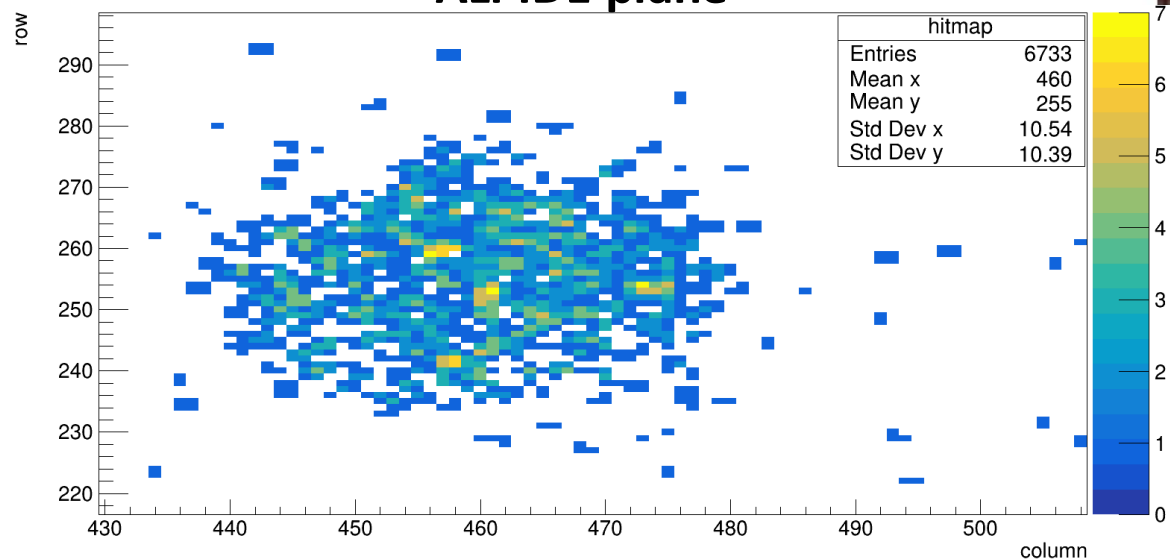


**1.5 mm**  
**(active 0.48 mm)**

# Testbeam setup – DESY September 2021

- 2 DPTS as DUTs
- New devices (not irradiated) at standard operation conditions (-1.2 V back bias)
- Scintillator with 1 mm hole (veto) to trigger on a narrower beam spot
- Moving stages to align hole scintillator and DUTs

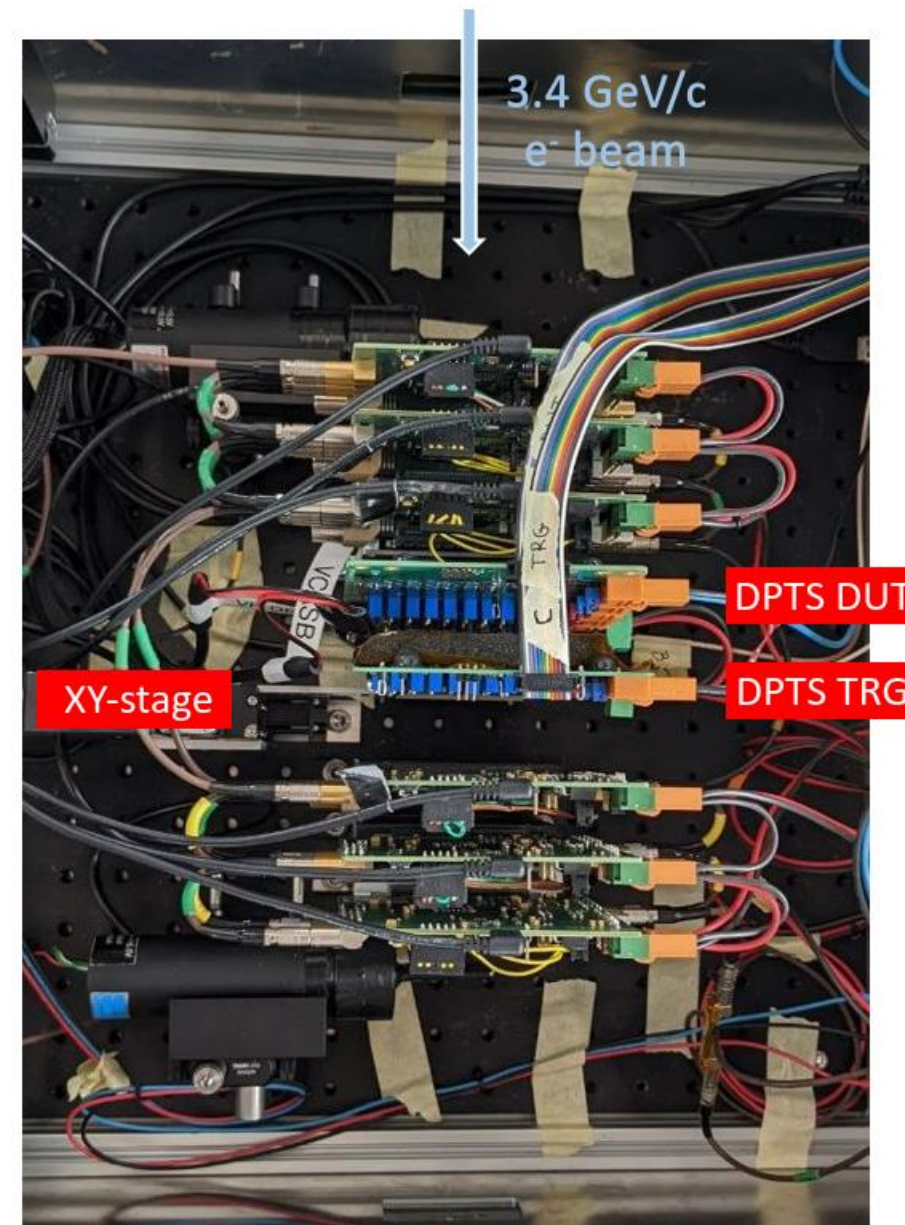
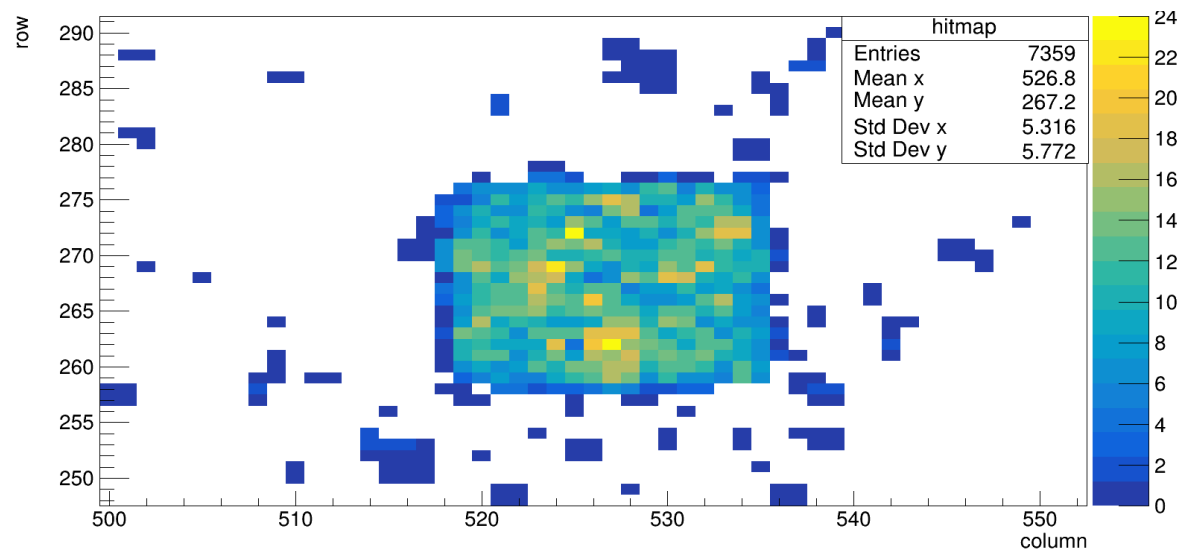
Scintillator hole as seen by the closest upstream ALPIDE plane





- DPTS DUT
- Different levels of irradiations at varying operation parameters
- One DPTS as trigger
- Moving stage to align DPTS trigger

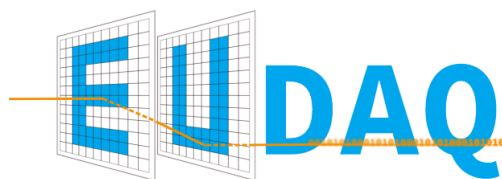
DPTS trigger as seen by the closest upstream ALPIDE plane





# Data acquisition and analysis

- DPTSs digital outputs are read out with a PC oscilloscope (picoScope)
- ALPIDE planes and picoscope are controlled and data acquired by using EUDAQ2



<https://github.com/eudaq/eudaq>

- Analysis is conducted with Corryvreckan



<https://gitlab.cern.ch/corryvreckan/corryvreckan>



# DPTS Readout features

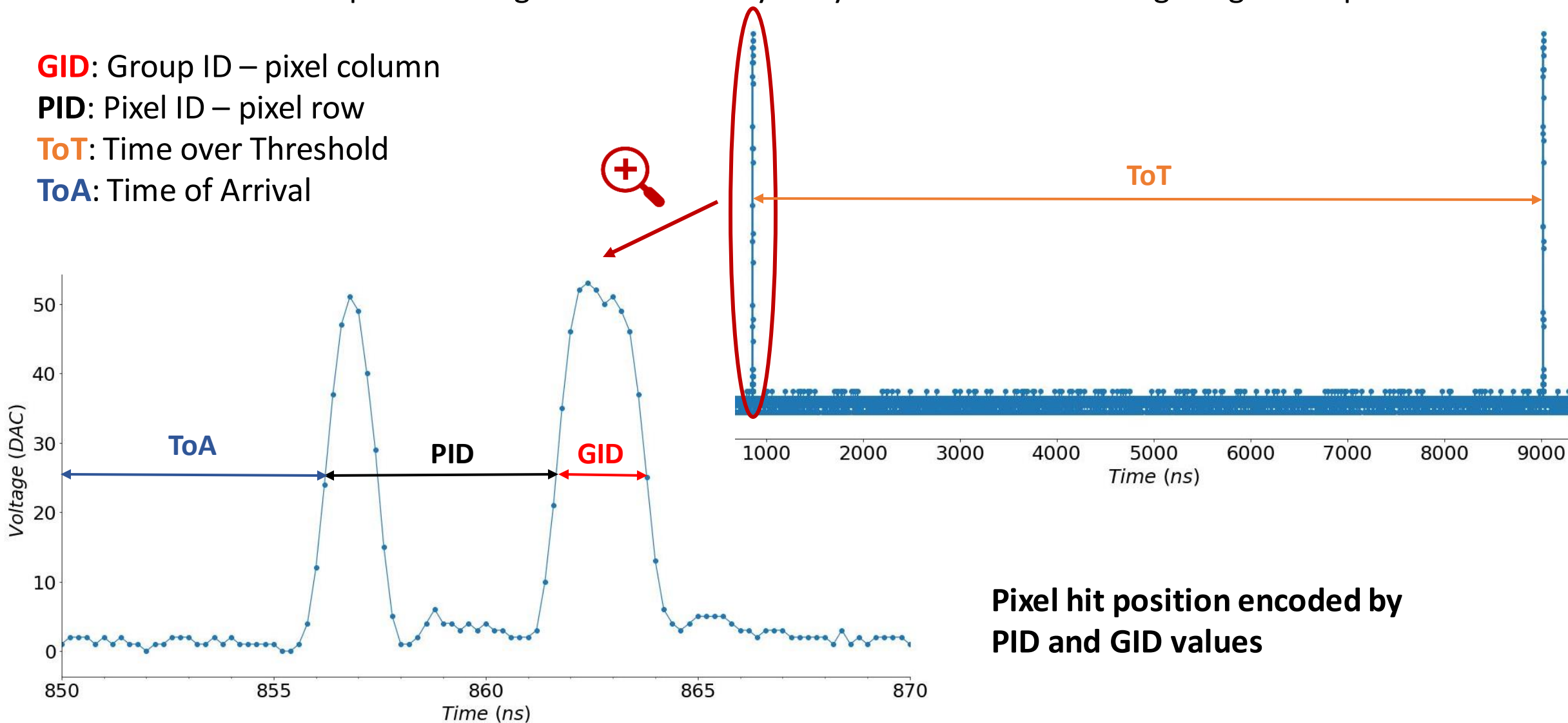
- The hits from all the pixels are digitized and conveyed by the readout into a single digital output

**GID:** Group ID – pixel column

**PID:** Pixel ID – pixel row

**ToT:** Time over Threshold

**ToA:** Time of Arrival

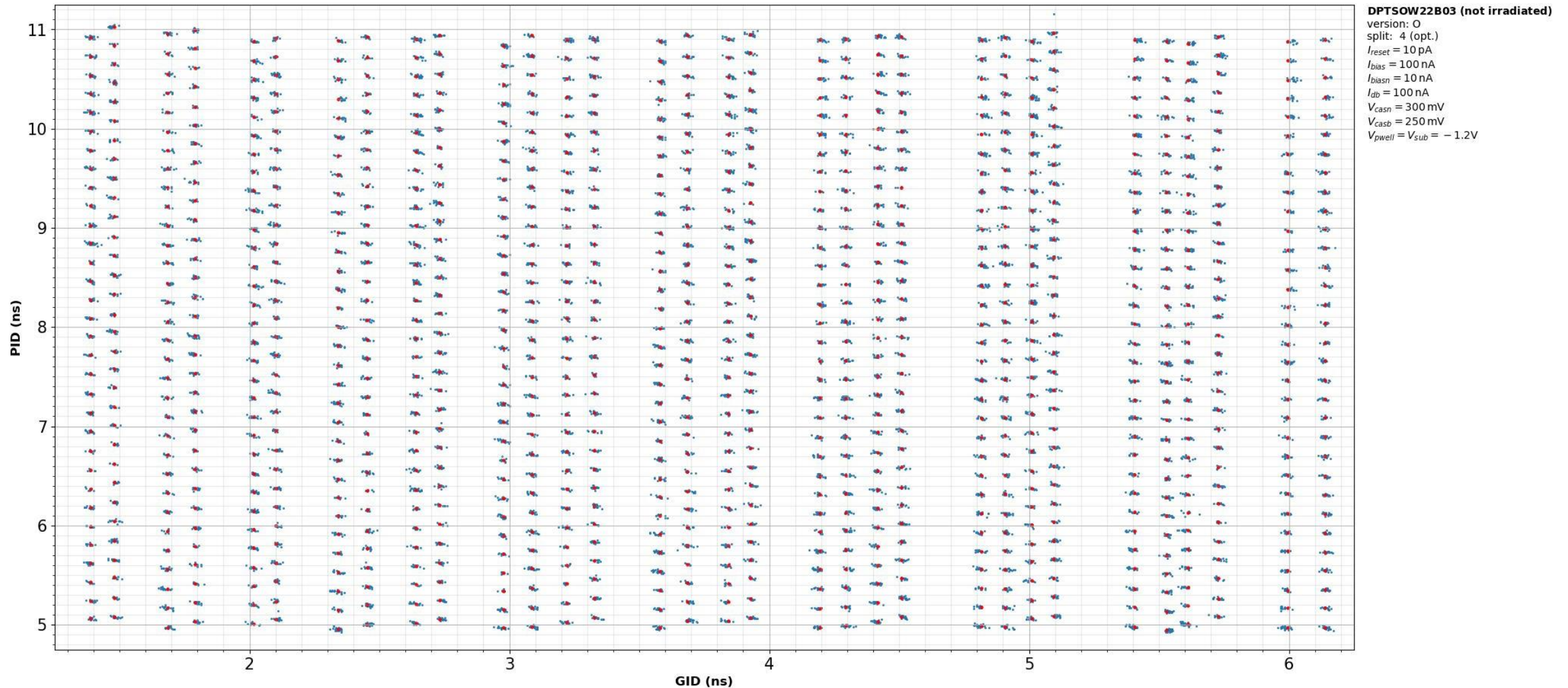


**Pixel hit position encoded by PID and GID values**



# Time to position decoding map

- Additional calibration file passed to Corryvreckan to address DPTS pulses decoding
- For each pulse, GID and PID are measured and hit is assigned to a pixel according to nearest neighbor logic



# Spatial residuals

- DESY September 2021 data: DPTSXW22B1, standard operation conditions
- Track selection:  $\chi^2/n_{dof} < 5$
- Spatial resolution  $O(4.3 \mu\text{m})$

**DPTSXW22B1 (not irradiated)**

version: X

split: 4 (opt.)

$I_{reset} = 10 \text{ pA}$

$I_{bias} = 100 \text{ nA}$

$I_{biasn} = 10 \text{ nA}$

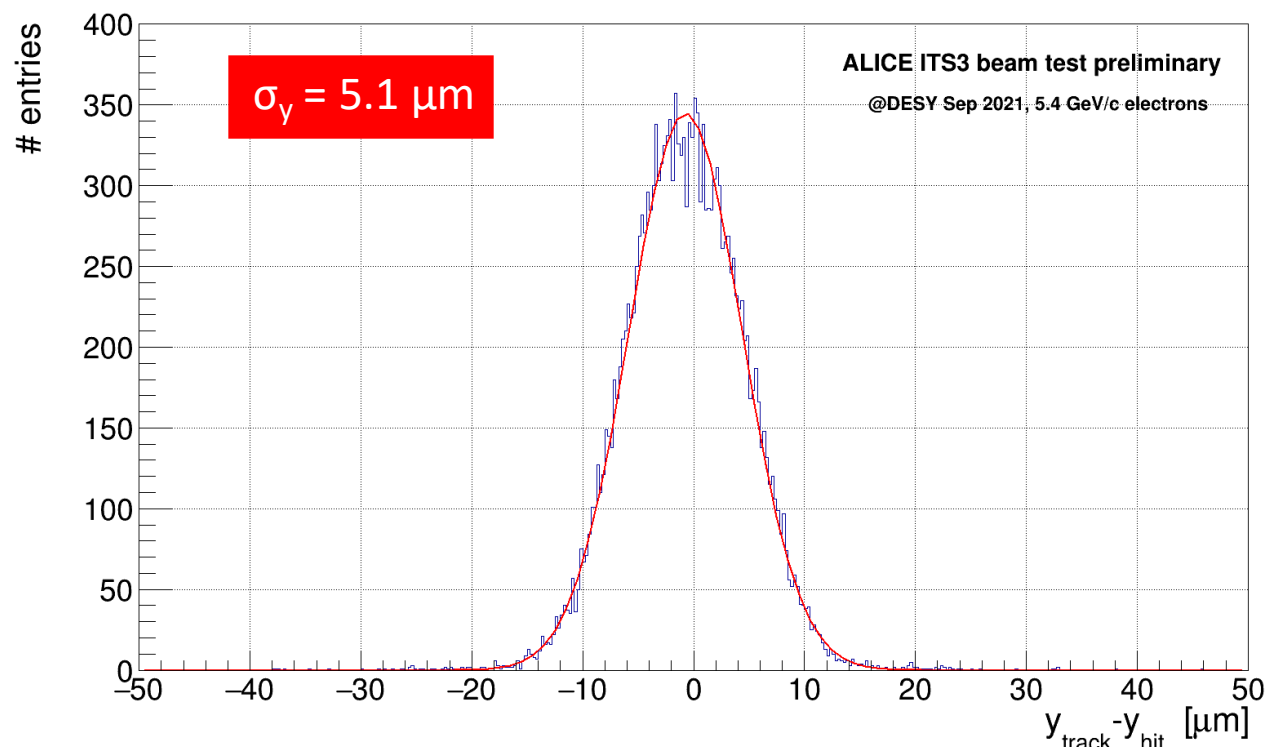
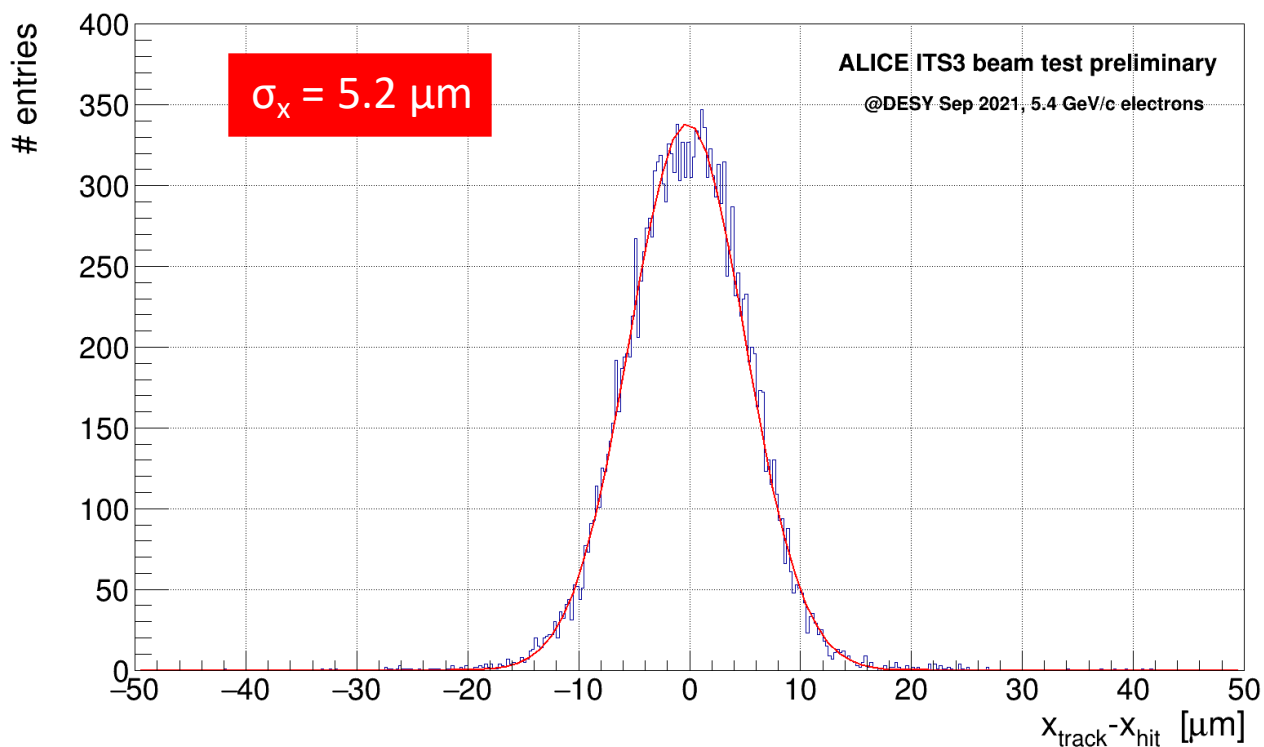
$I_{db} = 100 \text{ nA}$

$V_{casn} = 300 \text{ mV}$

$V_{casb} = 280 \text{ mV}$

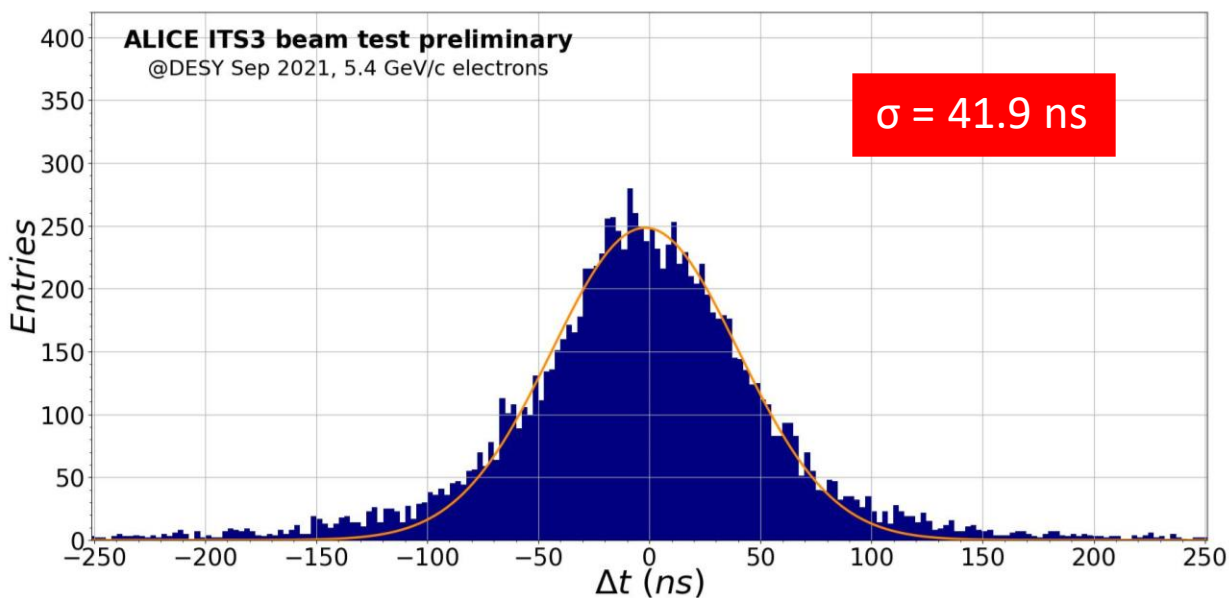
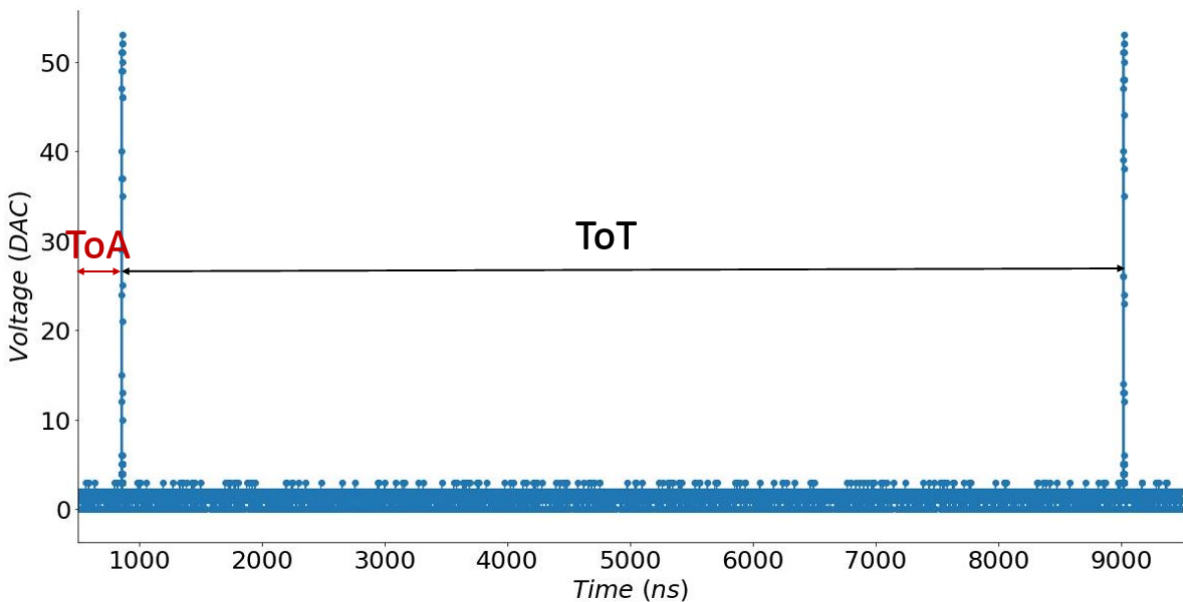
$V_{pwell} = V_{sub} = -1.2 \text{ V}$

$thr = 110e^-$





# Timing resolution - analysis

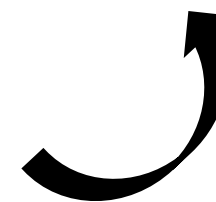
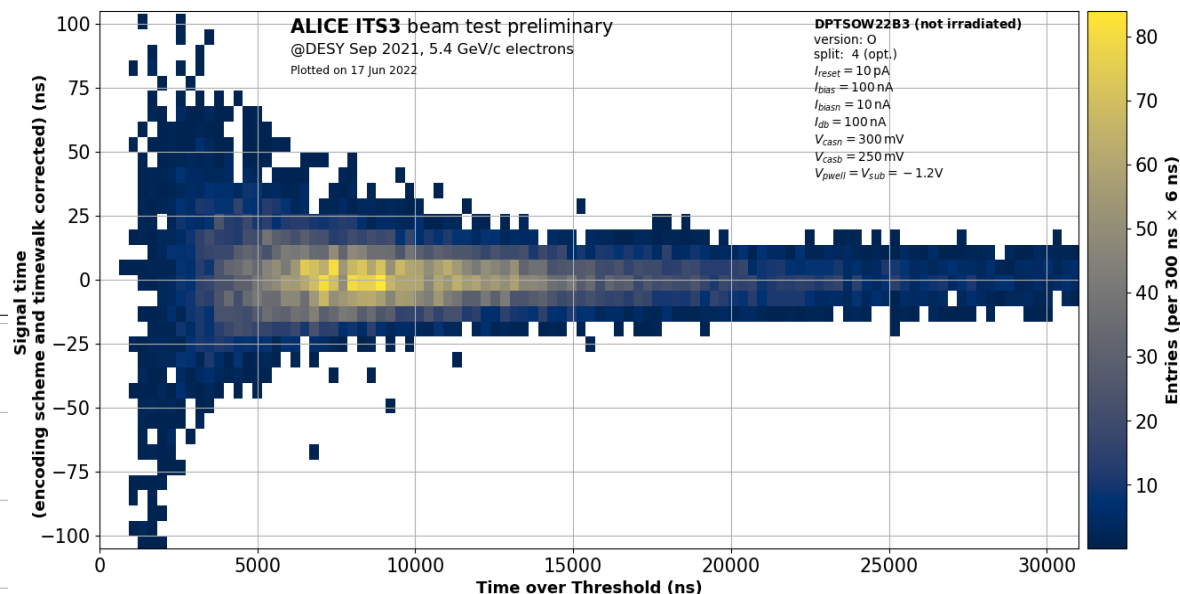
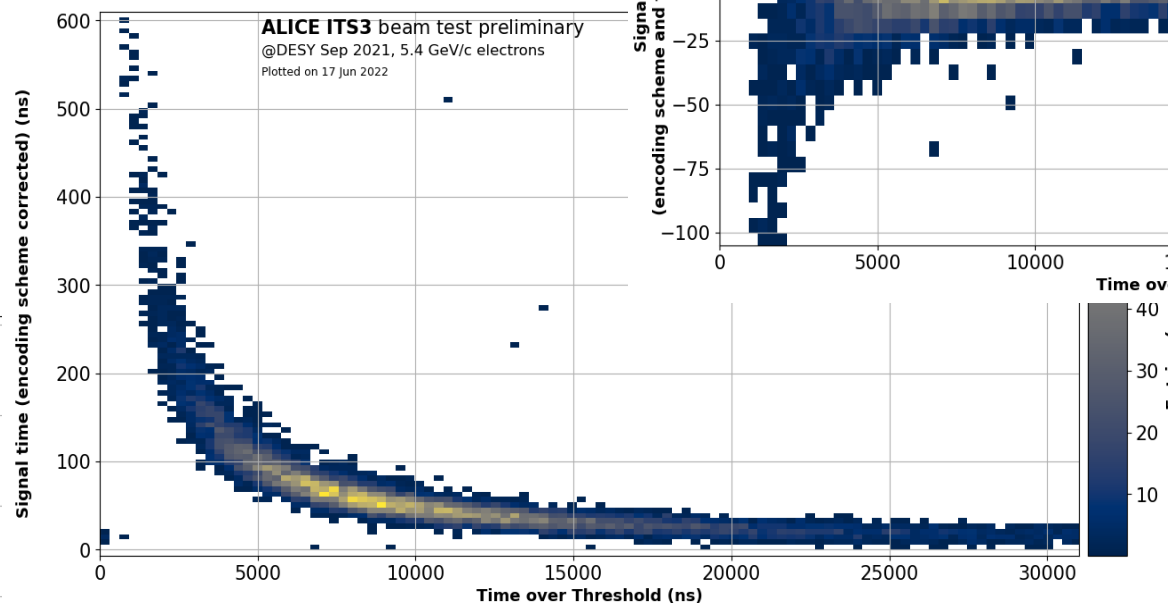
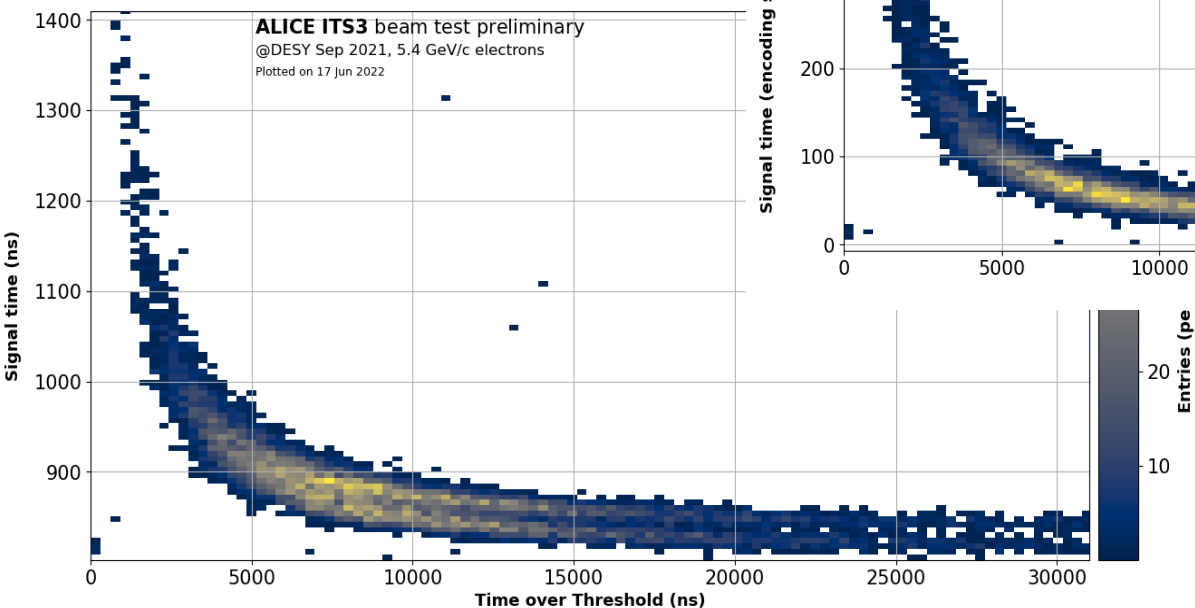
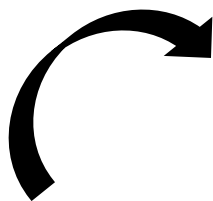


- DESY September 2021 data
- No timing layer in the ALPIDE telescope
- Only tracks associated to both DUT are considered
- Track selection:  $\chi^2/n_{dof} < 5$
- The timestamp is given by the Time of Arrival (ToA) of the pixel signal with respect to the trigger
- 2 timestamps per track
- **Time residuals distribution = ToA DPTS1 – ToA DPTS2**
- Corrections to be performed
  - Pixel encoding scheme
  - Timewalk correction

# Timing resolution - corrections

- Corrections applied separately to both devices

## Encoding scheme correction



## Timewalk correction

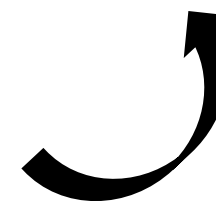
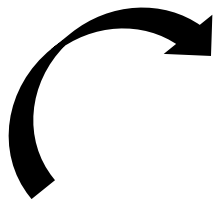
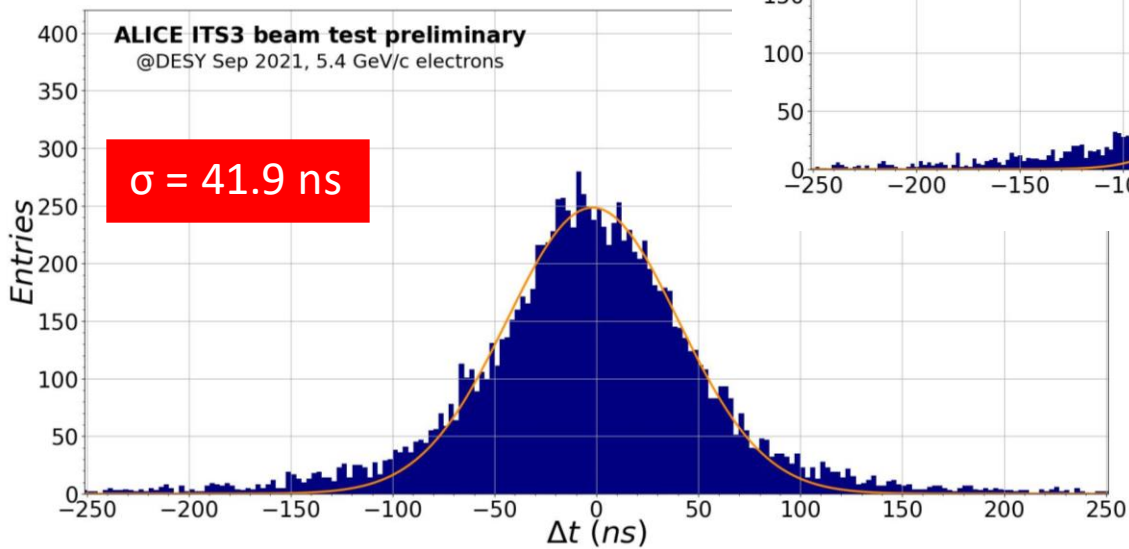
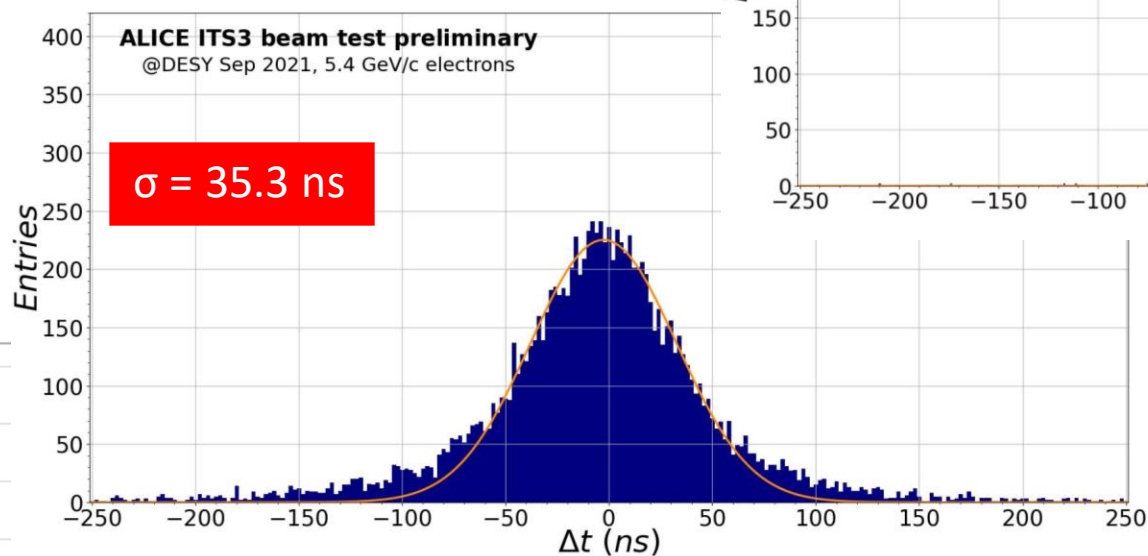
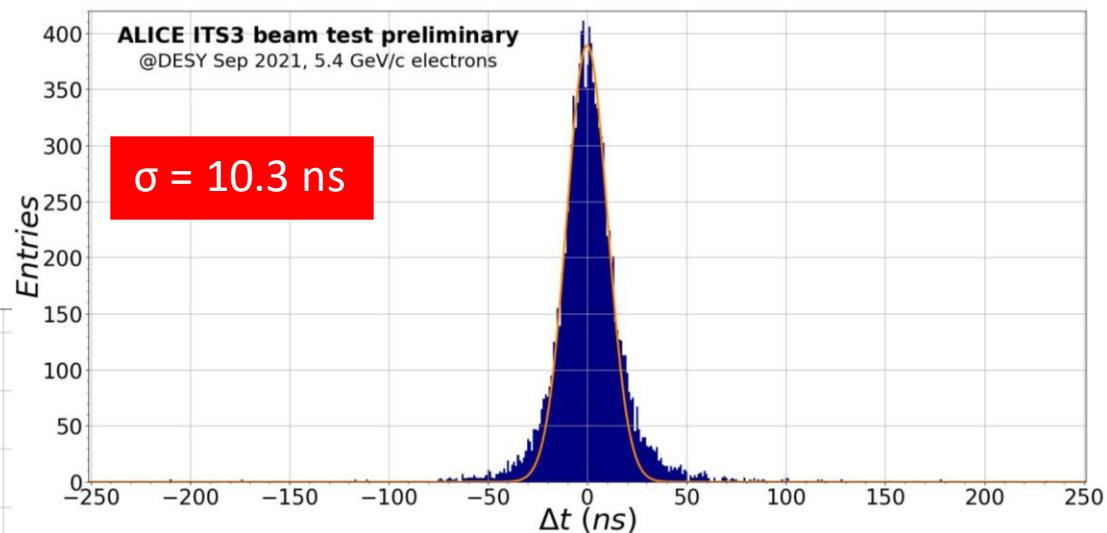
$$ToA = \frac{a}{ToT - t_0} + b$$



# Timing resolution - results

- Estimated sensor time resolution

$$\frac{10.3 \text{ ns}}{\sqrt{2}} = 7.3 \text{ ns}$$

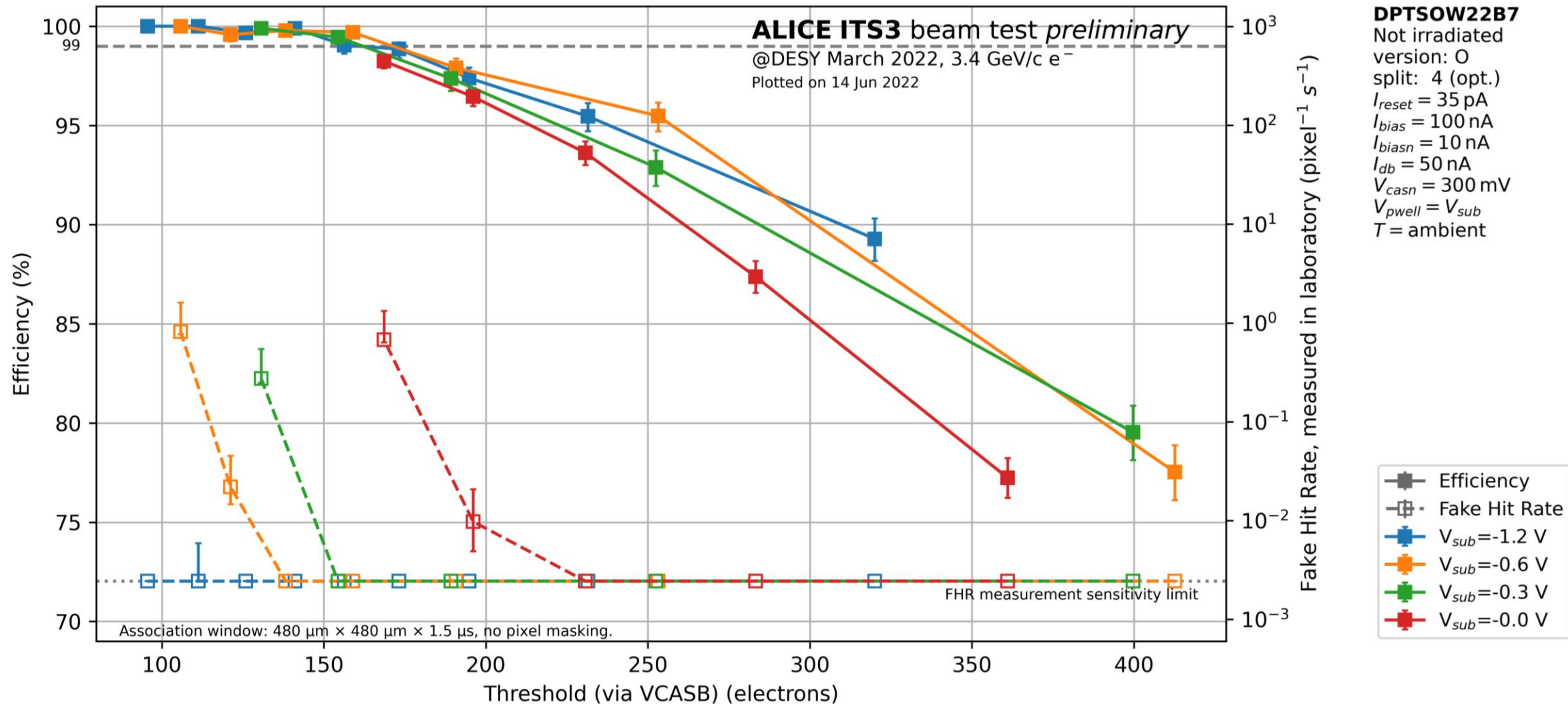


**Timewalk correction**

$$ToA = \frac{a}{ToT - t_0} + b$$

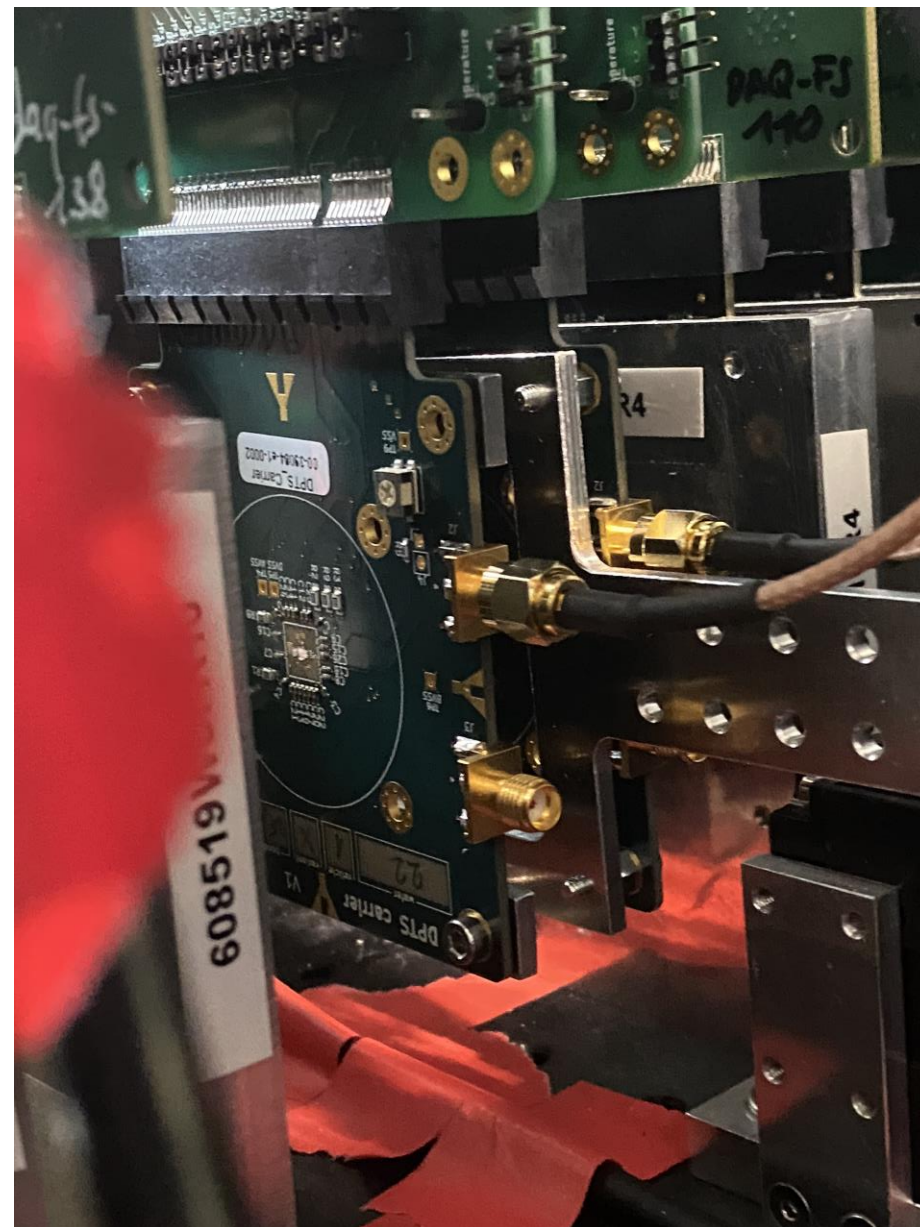
# Detection efficiency

- DESY March 2022 data: DPTSOW22B7, operation condition scan at room temperature
- Efficiency above 99.7% below 150 e<sup>-</sup> threshold at -1.2 V back bias





- DPTS is a MAPS fabricated in 65 nm CMOS imaging sensor technology
- Chip thoroughly tested during several testbeam campaigns
- Non-irradiated device under standard operation conditions:
  - Spatial residuals  $O(5 \mu\text{m})$
  - Time residuals  $O(10 \text{ ns})$
  - Detection efficiency above 99.7%
- Performance figures of first prototype are very promising for the ITS3 requirements



- Irradiated devices analysis ongoing (NIEL irradiation levels from  $10^{13}$  to  $10^{15}$   $1 \text{ MeV n}_{\text{eq}} \text{ cm}^{-2}$ )
- In-pixel efficiency studies
- Another testbeam (at CERN PS) data taking has just concluded:
  - Studied chip behavior under controlled temperature
  - Studied new operation conditions (larger back-bias range, up to  $-3 \text{ V}$ )
  - Analysis ongoing



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**Big thank you to the DESY testbeam support team!**



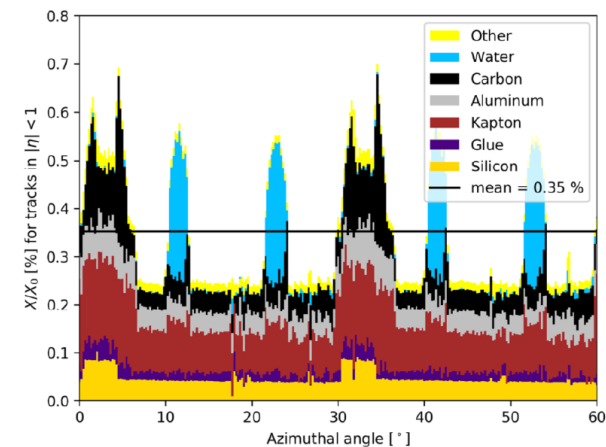
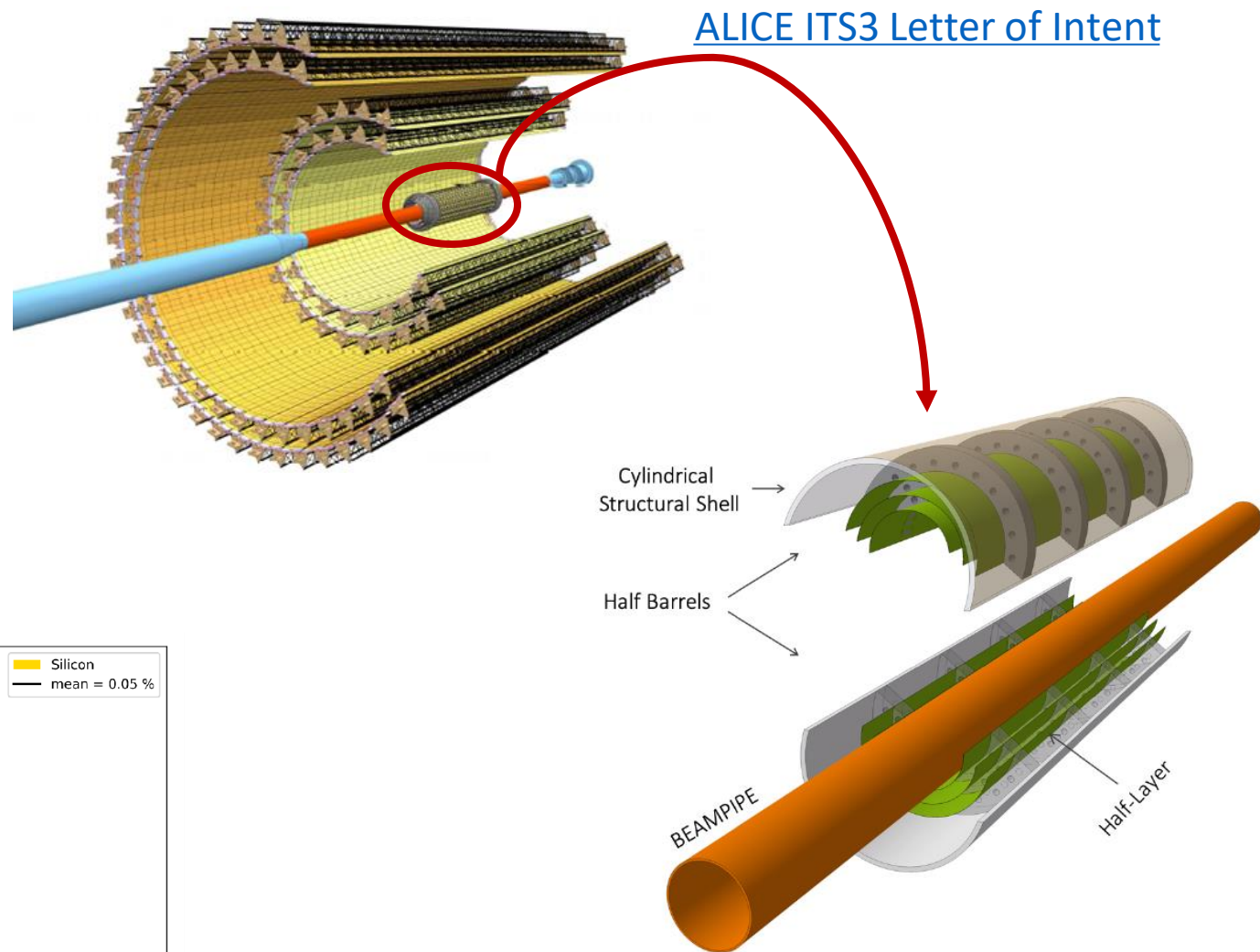
The measurements leading to the shown results have been performed at the Test Beam Facility at DESY Hamburg (Germany), a Member of the Helmholtz Association (HGF)

**Additional slides**

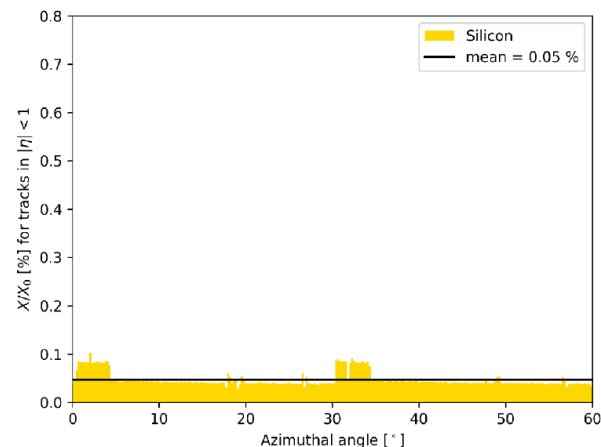


# ALICE Inner Tracking System 3 (ITS3)

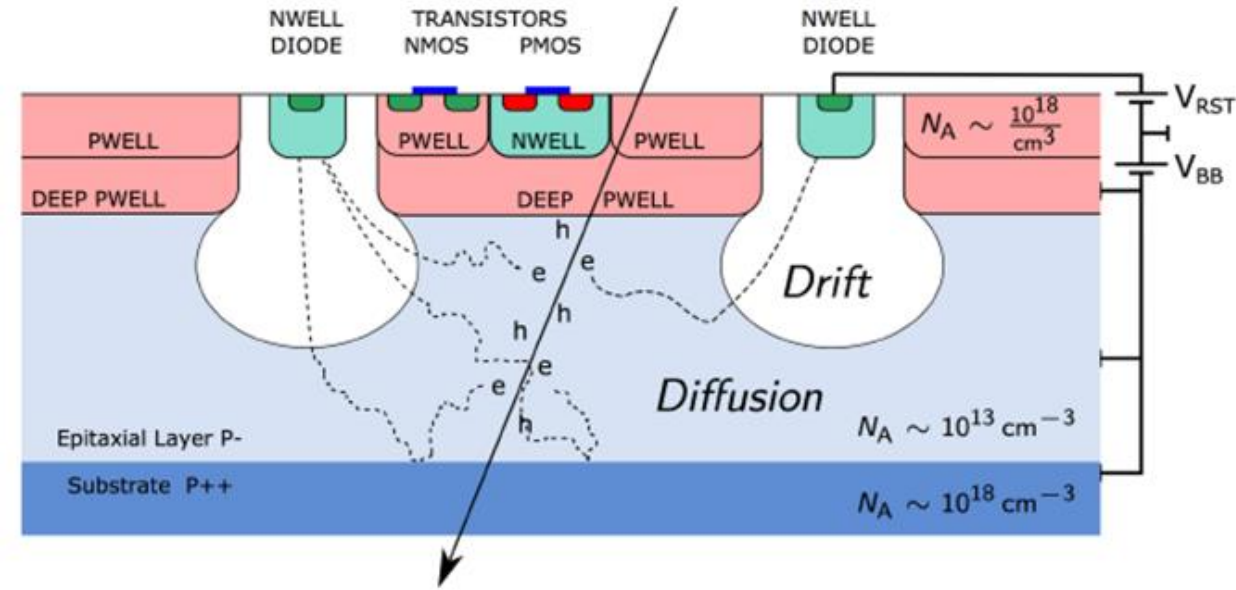
- Improve vertexing at high rate and low transverse momentum
- Replace the 3 layers of the ITS Inner Barrel
  - Fully cylindrical layers with radii of 18/24/30 mm around the beam pipe
- Design based on wafer-scale bent MAPS thinned down to 20-40  $\mu\text{m}$
- Target technology: 65 nm CMOS sensors
- “Moderate” radiation hardness requirements
  - NIEL:  $10^{14}$  1 MeV  $n_{\text{eq}}/\text{cm}^2$
  - TID: 10 MRad



ITS2 Layer 0:  $X/X_0 = 0.35$

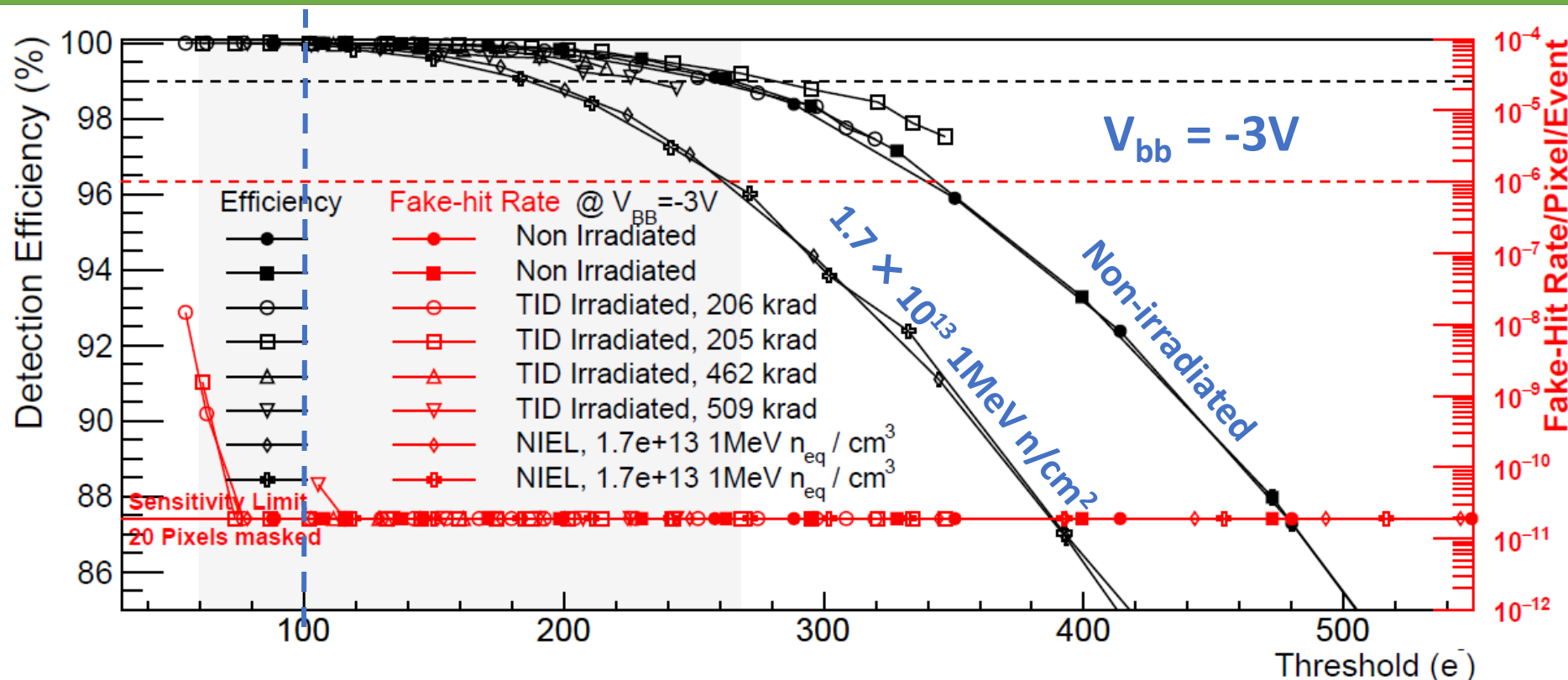


ITS3 Layer 0:  $X/X_0 = 0.05$



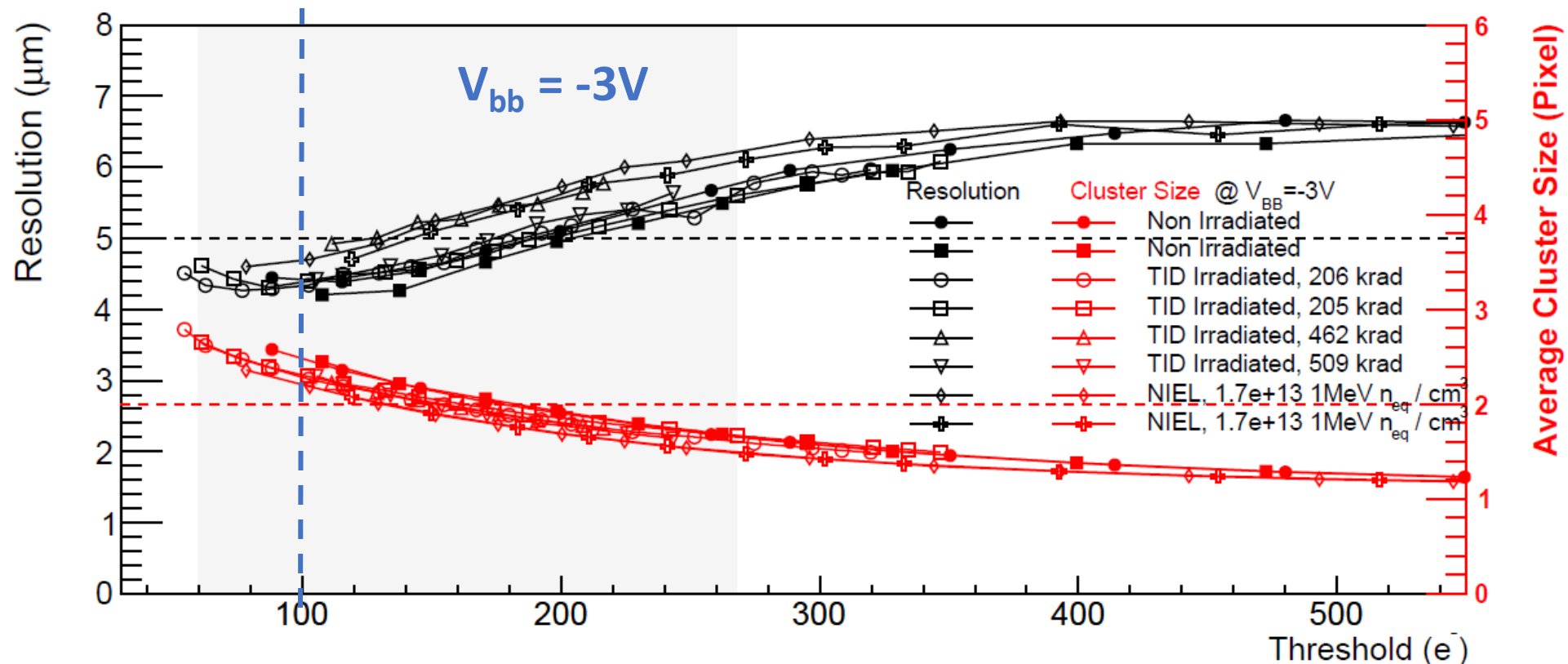
- TowerJazz 180 nm CMOS Standard Imaging Process pixel sensor:
  - High-resistivity ( $> 1 \text{ k}\Omega\cdot\text{cm}$ ) p-type epitaxial layer ( $25 \mu\text{m}$ ) on p-type substrate
  - $2 \mu\text{m}$  diameter n-well electrode,  $\sim 5 \text{ pF}$  input capacitance
  - **$50 \mu\text{m}$  overall sensor thickness**
- Monolithic design:
  - In pixel amplification, discrimination, 3 hit storage registers
- Ultra-low power consumption:
  - **$40 \text{ nW/pixel}$**
  - **$20 \text{ mW/cm}^2$**
- High hit rate transmission:
  - **$\sim 6 \text{ MHz/cm}^2$  hit rate chip output data transfer**





- Measured with 6 GeV/c pion beam
- At 100  $e^-$  of operation threshold and  $V_{bb} = -3 V$ :
  - Detection efficiency above 99.99%
  - Fake hit rate  $< 2 \times 10^{-11}$  pixel hits/event
  - Irradiated chips performance is comparable with not-irradiated chips

# ALPIDE performance figures

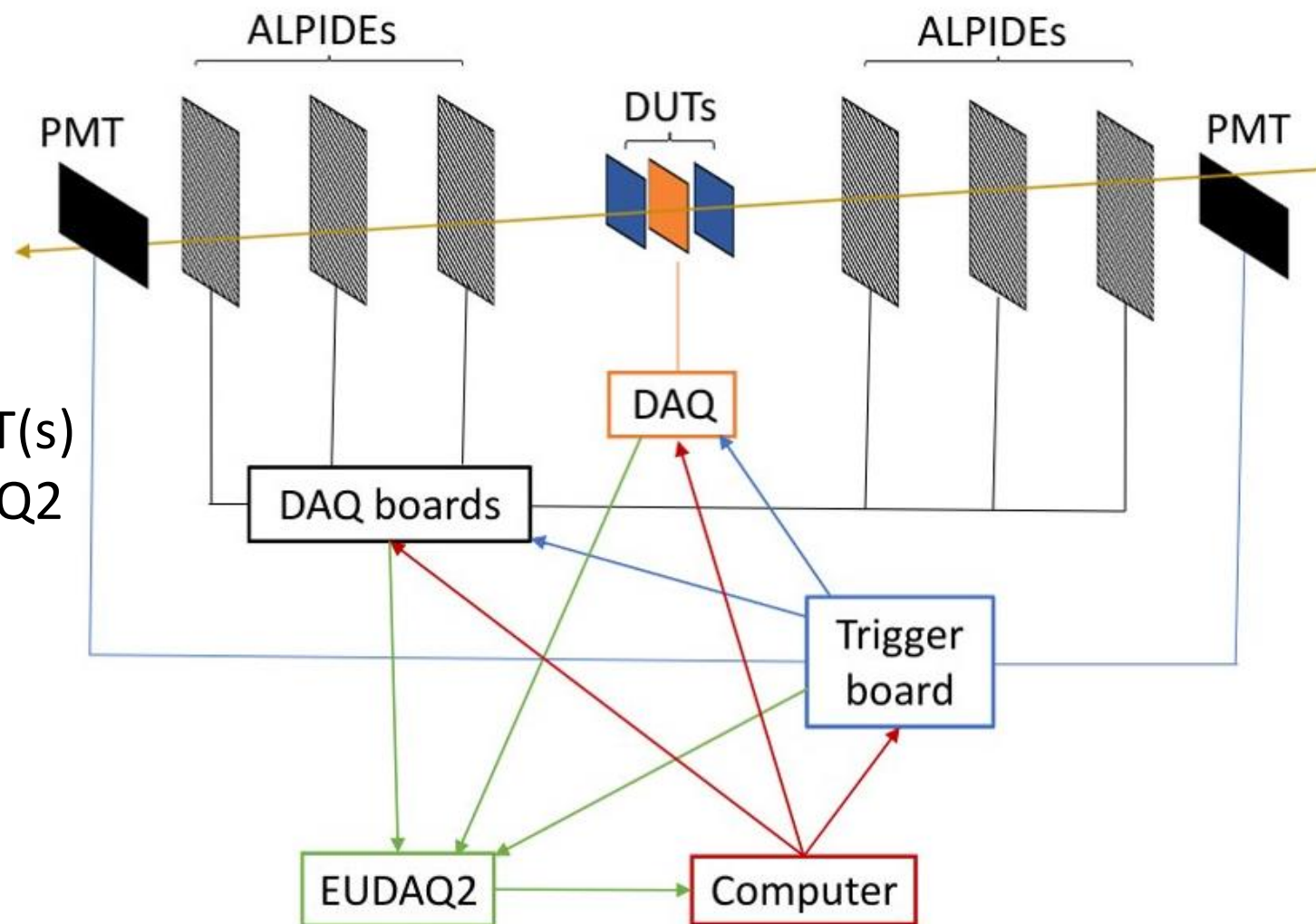


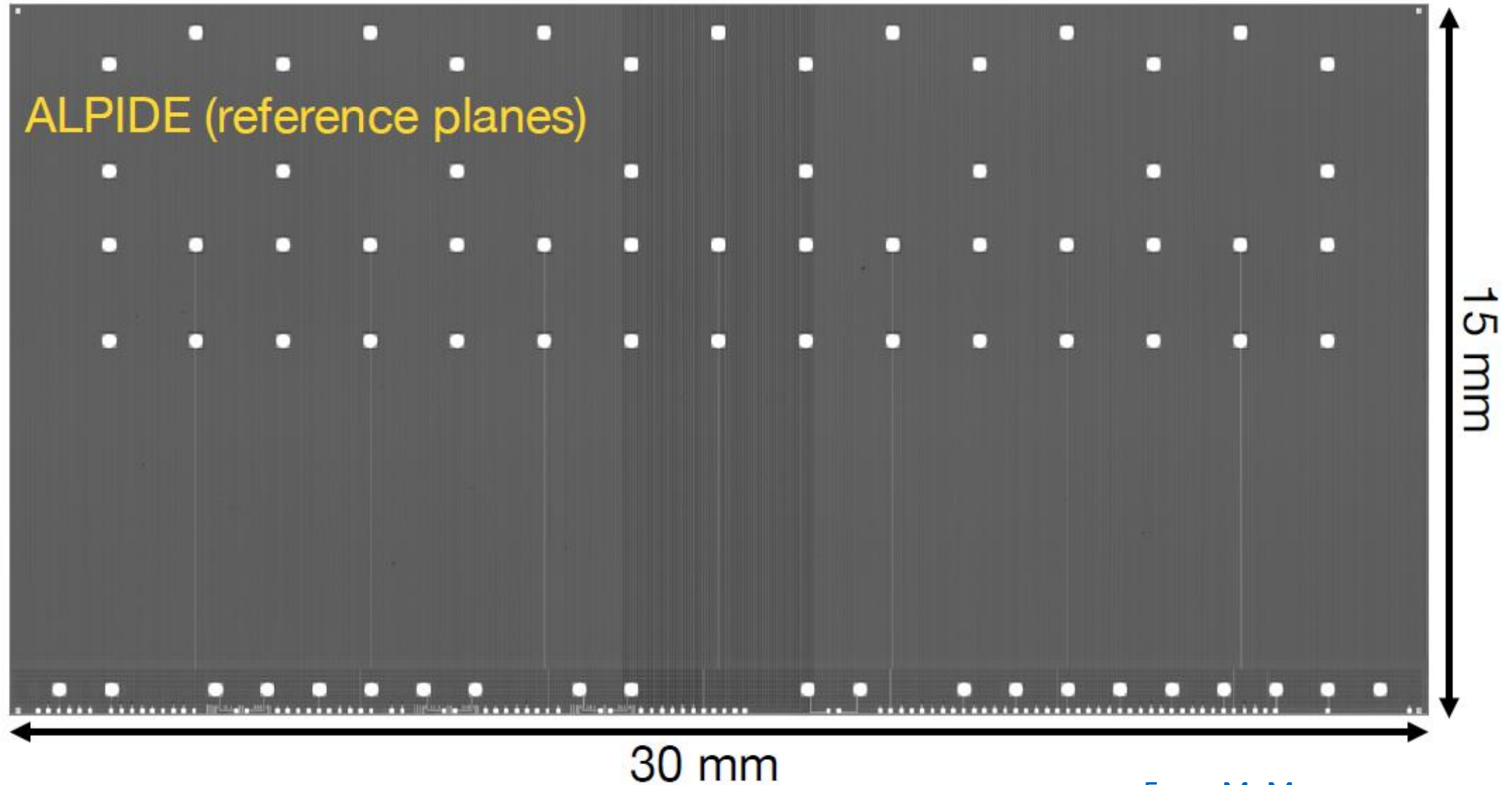
- Measured with 6 GeV/c pion beam
- At  $100 e^-$  of operation threshold and  $V_{bb} = -3 V$ :
  - Spatial resolution below  $5 \mu\text{m}$
- Not irradiated and TID/NIEL chips show similar performance



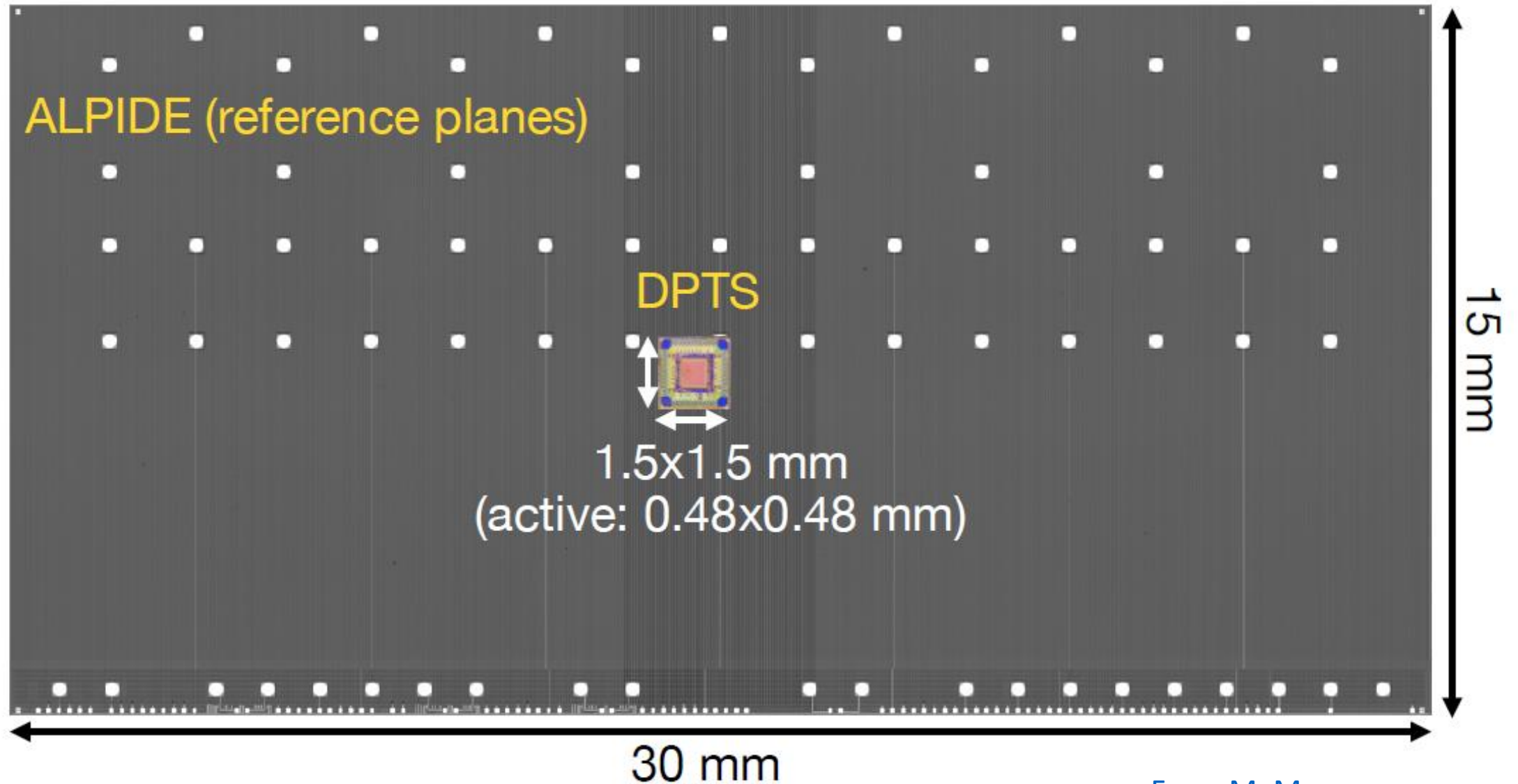
# The ALPIDE telescope

- High flexibility and portability
- 6 ALPIDE tracking planes as standard configuration
- ALPIDE DAQ board based on FPGA
- Custom trigger board
- Movable XY stages for DUT(s) and PMT(s)
- Data acquisition integrated into EUDAQ2



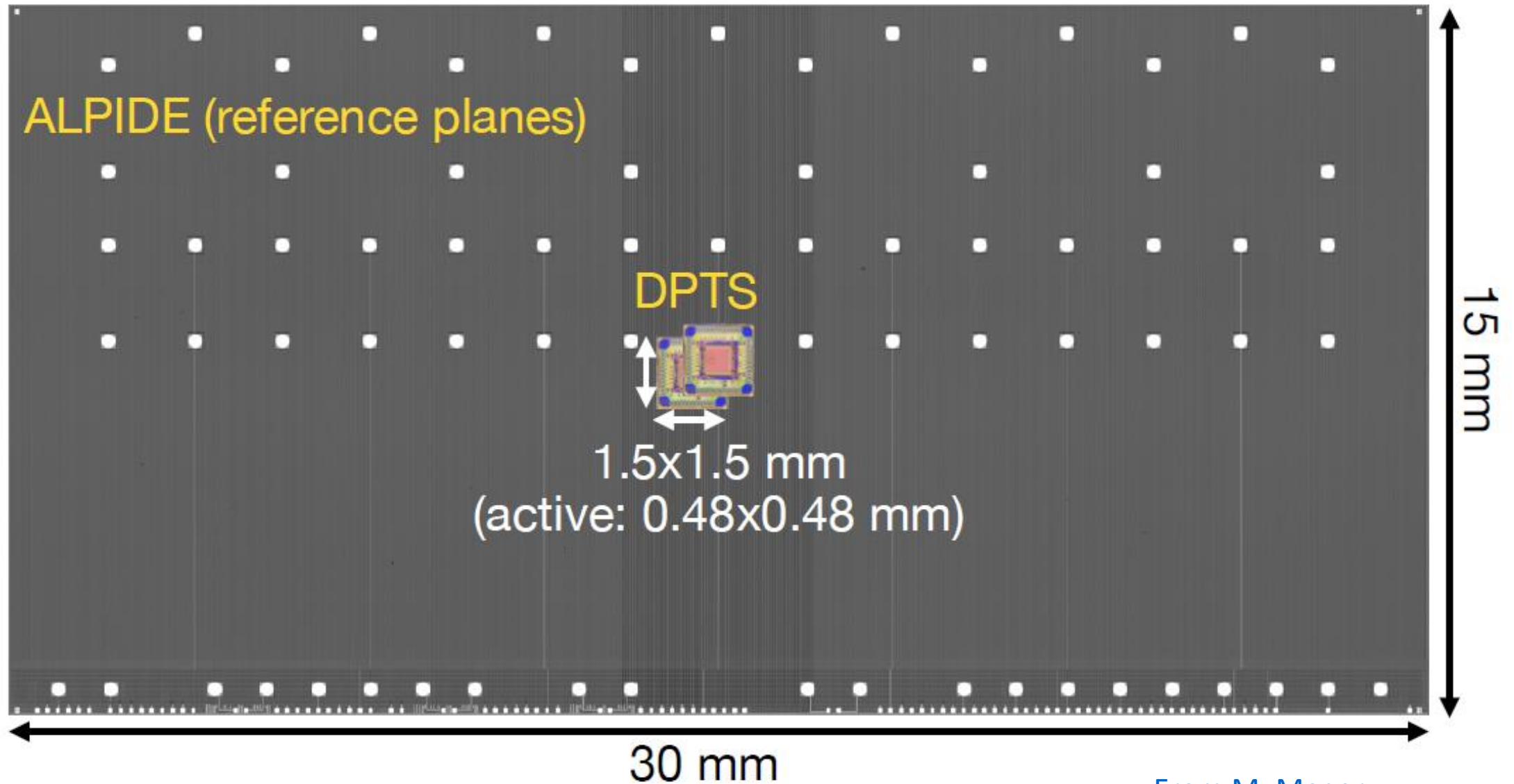


[From M. Mager](#)

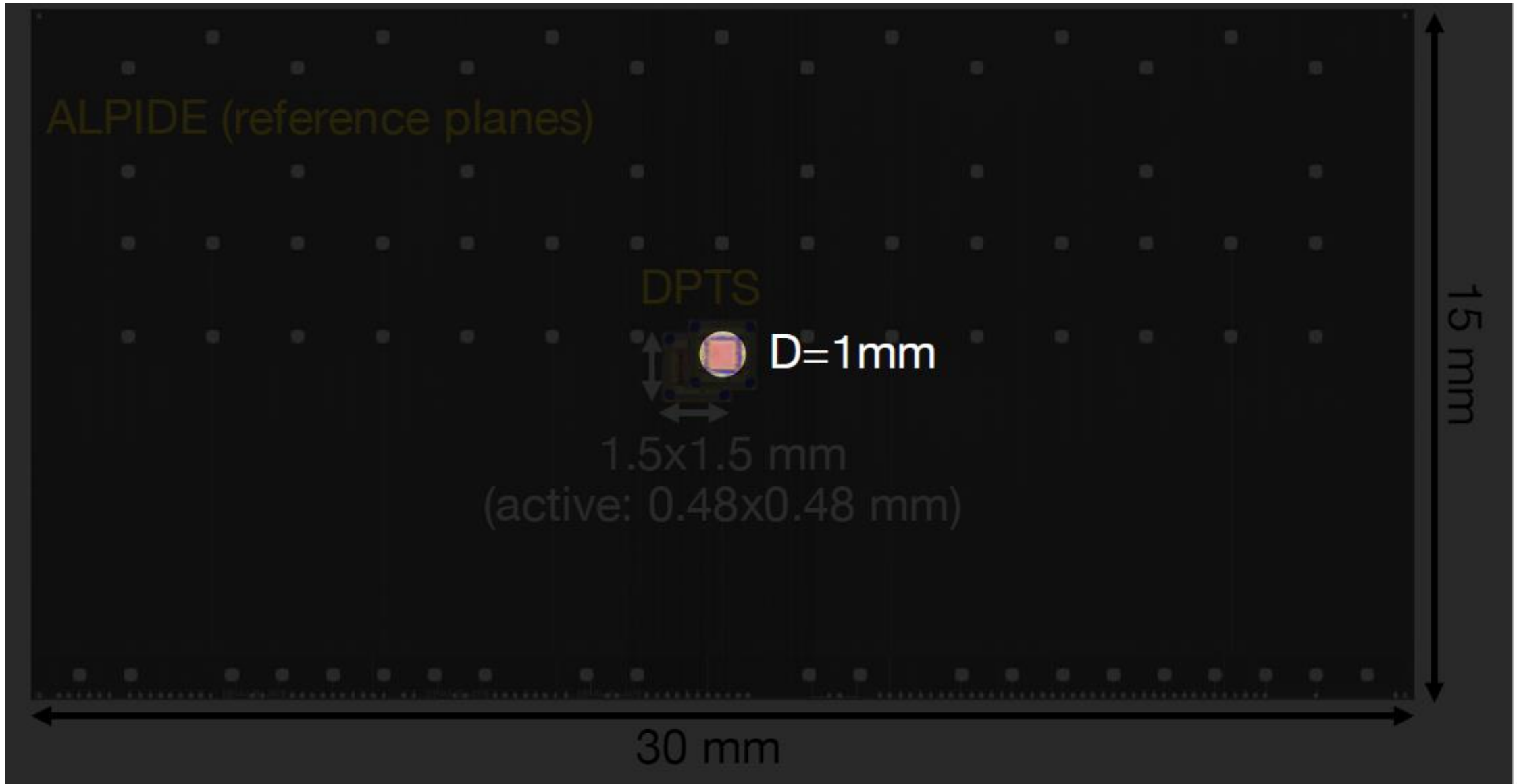


[From M. Mager](#)





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DPTSOW22B03 GID/ToA correlation

